Abstracts

New Distributed Amplifier Design Using Transmission-Gate FET's

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Y. Imai, S. Kimura, Y. Umeda and T. Enoki. "New Distributed Amplifier Design Using Transmission-Gate FET's." 1996 Microwave and Guided Wave Letters 6.10 (Oct. 1996 [MGWL]): 357-359.

We propose a new distributed amplifier design using a transmission-gate FET (TGFET) whose gate is embedded in the gate-artificial line. The new technique greatly simplifies the gate-artificial-line design, with no meandering or T-junction lines. The test TGFET distributed amplifier, using 0.1-µm-gate-length InP HEMT's showed a promising bandwidth performance of 100 GHz.

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